



# PSMN0R7-25YLD

N-channel 25 V, 0.72 mΩ, 300 A logic level MOSFET in LPAK56 using NextPowerS3 Technology

25 July 2017

Product data sheet

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LPAK56 package. NextPowerS3 portfolio utilising NXP's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETS with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

## 2. Features and benefits

- 100% Avalanche tested at  $I_{(AS)} = 190$  A
- Ultra low  $Q_G$ ,  $Q_{GD}$  and  $Q_{OSS}$  for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with  $< 1$   $\mu$ A leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 150 °C
- Wave solderable; exposed leads for optimal visual solder inspection

## 3. Applications

- On-board DC:DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control
- Power OR-ing

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 150\text{ °C}$		-	-	25	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	[1]	-	-	300	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>		-	-	158	W
<b>Static characteristics</b>							
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>		-	0.76	0.92	mΩ

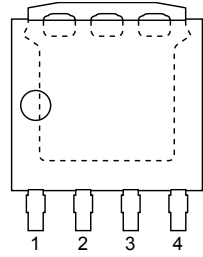
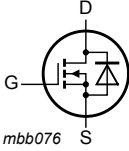
N-channel 25 V, 0.72 mΩ, 300 A logic level MOSFET in LPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	11.9	-	nC

[1] 300A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB thermal design and operating temperature

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK56; Power-SO8 (SOT1023)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	Gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN0R7-25YLD	LPAK56; Power-SO8	Plastic single-ended surface-mounted package (LPAK56); 4 leads	SOT1023

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN0R7-25YLD	0D725L

## 8. Limiting values

Table 5. Limiting values

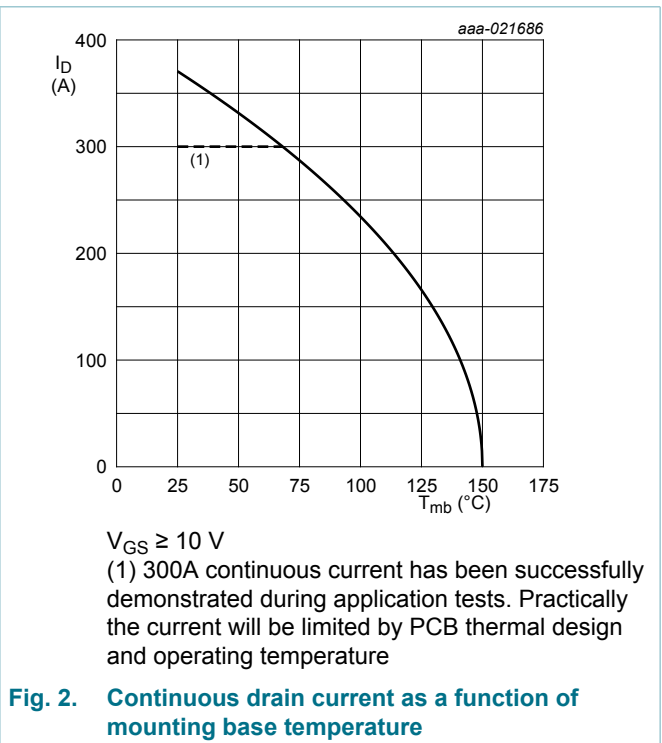
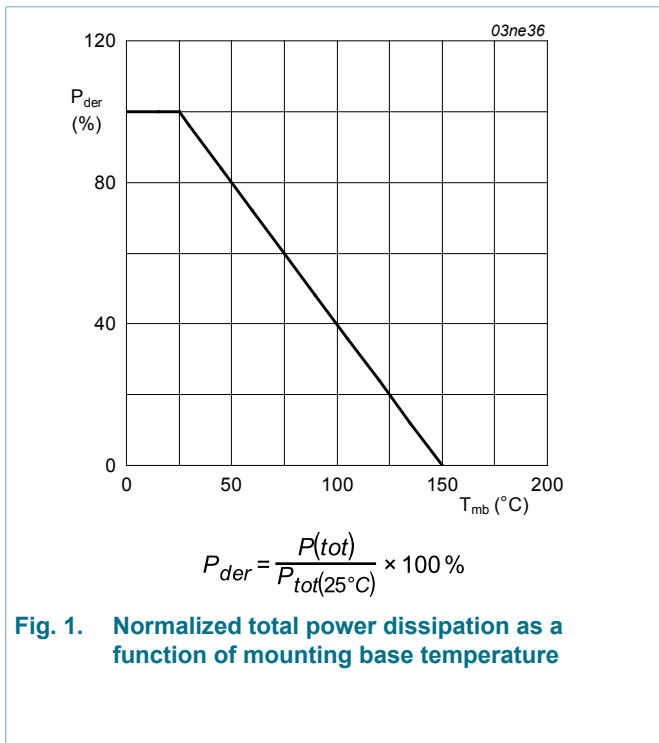
In accordance with the Absolute Maximum Rating System (IEC 60134).

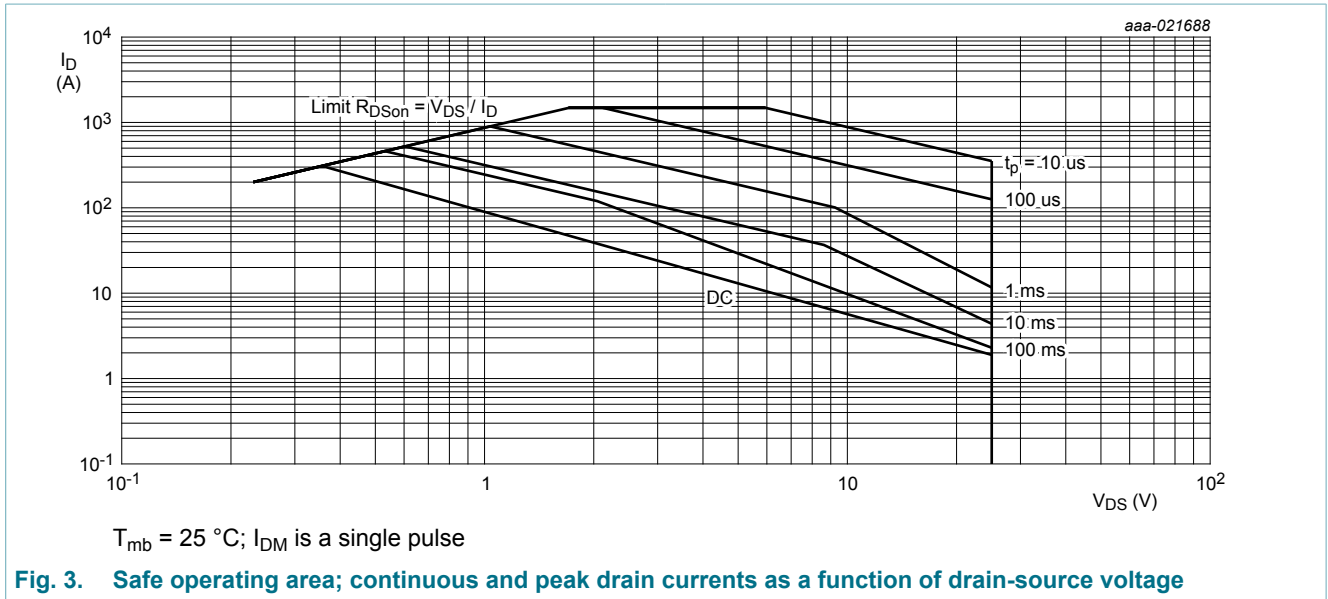
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	25	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 150 °C; R <sub>GS</sub> = 20 kΩ	-	25	V
V <sub>GS</sub>	gate-source voltage		-20	20	V

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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; Fig. 1		-	158	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; Fig. 2	[1]	-	300	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C		-	235	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; Fig. 3		-	1482	A
T <sub>stg</sub>	storage temperature			-55	150	°C
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>slid(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	HBM		2	-	kV
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	132	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	1482	A
<b>Avalanche ruggedness</b>						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 300 A; V <sub>sup</sub> ≤ 25 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; t <sub>p</sub> = 36 μs		-	174	mJ
I <sub>AS</sub>	non-repetitive avalanche current	V <sub>sup</sub> ≤ 25 V; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω	[2]	-	190	A

- [1] 300A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB thermal design and operating temperature
- [2] Protected by 100% test

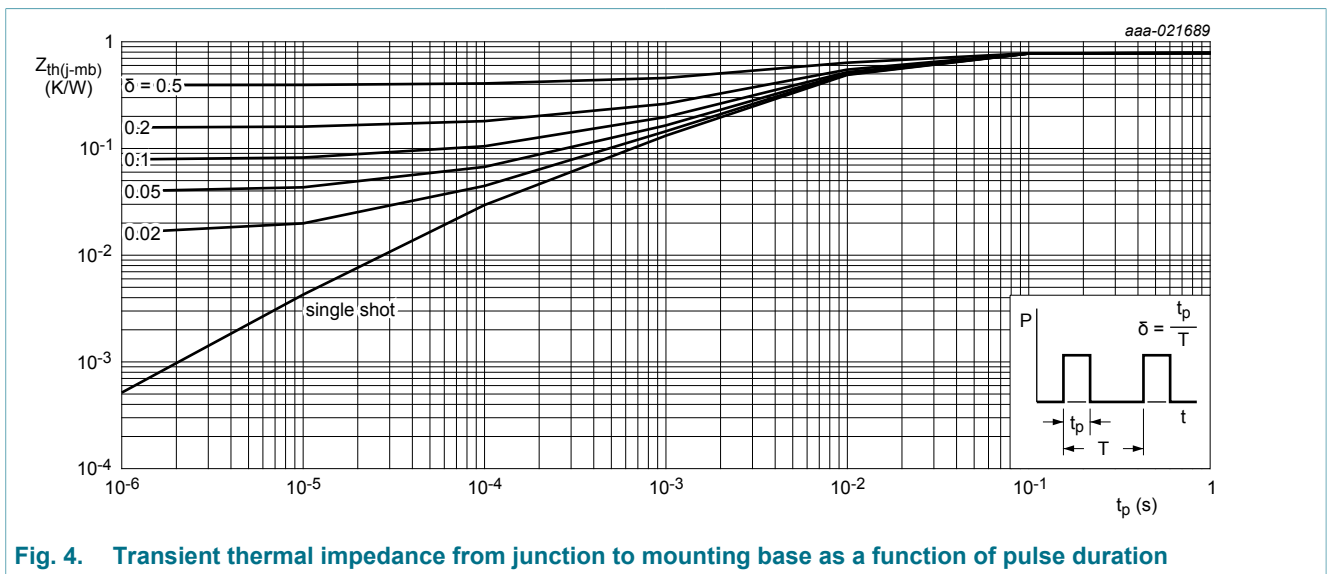


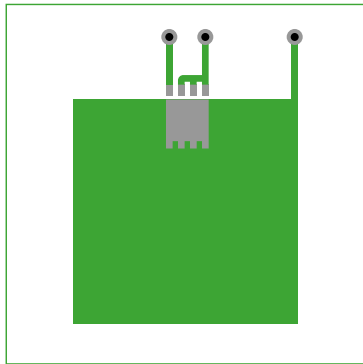


## 9. Thermal characteristics

Table 6. Thermal characteristics

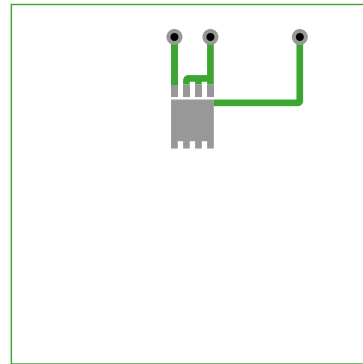
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 4</a>	-	0.59	0.79	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	<a href="#">Fig. 5</a>	-	50	-	K/W
		<a href="#">Fig. 6</a>	-	125	-	K/W





aaa-005750

Fig. 5. PCB layout for thermal impedance junction to ambient 1" square pad; FR4 Board; 2oz copper



aaa-005751

Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

## 10. Characteristics

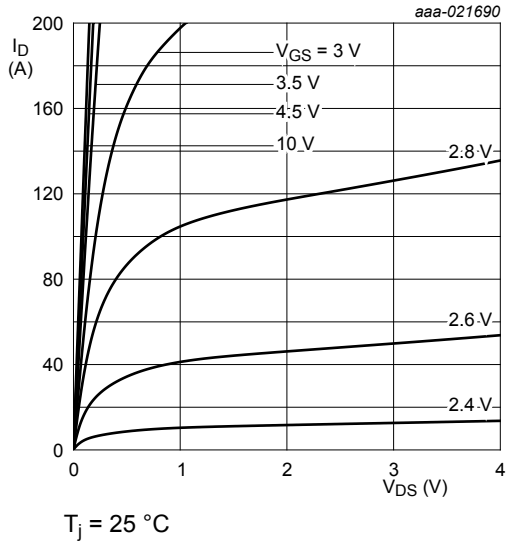
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	25	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.2	1.66	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	-5.1	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	68.5	-	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	0.76	0.92	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C;$ <a href="#">Fig. 10; Fig. 11</a>	-	-	1.47	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	0.57	0.72	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C;$ <a href="#">Fig. 10; Fig. 11</a>	-	-	1.15	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	1.35	-	Ω

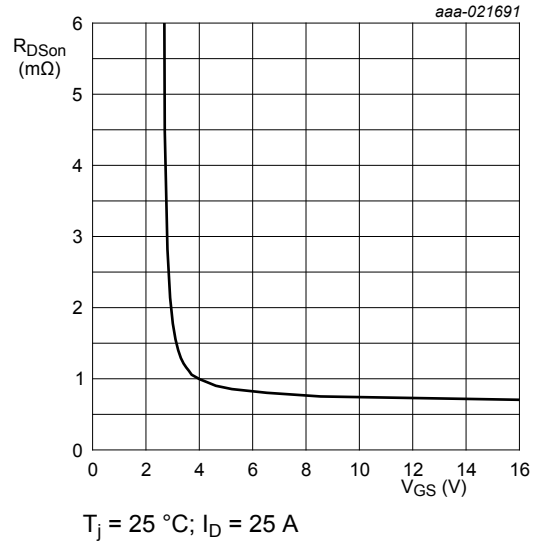
## N-channel 25 V, 0.72 mΩ, 300 A logic level MOSFET in LPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Dynamic characteristics</b>							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	110.2	-	nC	
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	50.9	-	nC	
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	45.8	-	nC	
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	18.8	-	nC	
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	11.9	-	nC	
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	6.9	-	nC	
Q <sub>GD</sub>	gate-drain charge		-	11.9	-	nC	
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	2.6	-	V	
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a>	-	8320	-	pF	
C <sub>oss</sub>	output capacitance		-	2982	-	pF	
C <sub>rss</sub>	reverse transfer capacitance		-	522	-	pF	
t <sub>d(on)</sub>	turn-on delay time		V <sub>DS</sub> = 12 V; R <sub>L</sub> = 0.6 Ω; V <sub>GS</sub> = 4.5 V; R <sub>G(ext)</sub> = 5 Ω	-	42.2	-	ns
t <sub>r</sub>	rise time		-	48.3	-	ns	
t <sub>d(off)</sub>	turn-off delay time		-	53.1	-	ns	
t <sub>f</sub>	fall time		-	38.2	-	ns	
Q <sub>oss</sub>	output charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 12 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	54	-	nC	
<b>Source-drain diode</b>							
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>	-	0.77	1.2	V	
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 12 V; <a href="#">Fig. 16</a>	-	57.7	-	ns	
Q <sub>r</sub>	recovered charge		[1]	-	83.2	-	nC
t <sub>a</sub>	reverse recovery rise time		-	-	30.5	-	ns
t <sub>b</sub>	reverse recovery fall time		-	-	27.2	-	ns
S	softness factor		-	-	0.9	-	

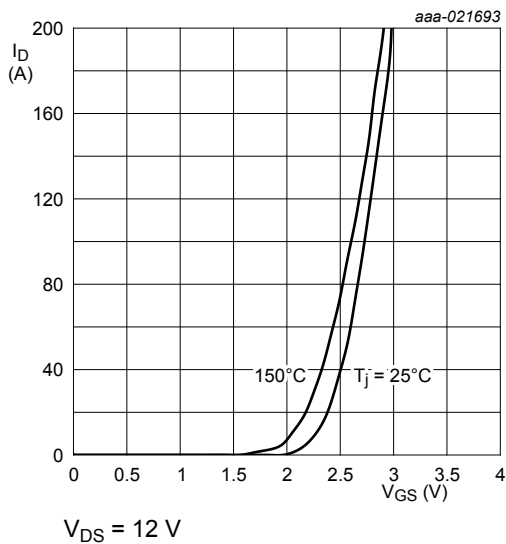
[1] includes capacitive recovery



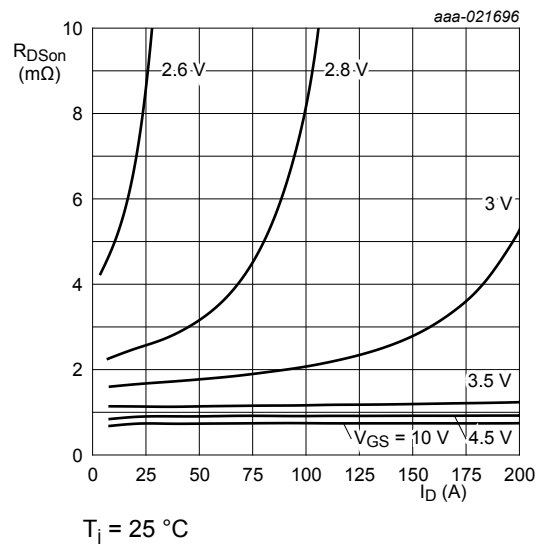
**Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values**



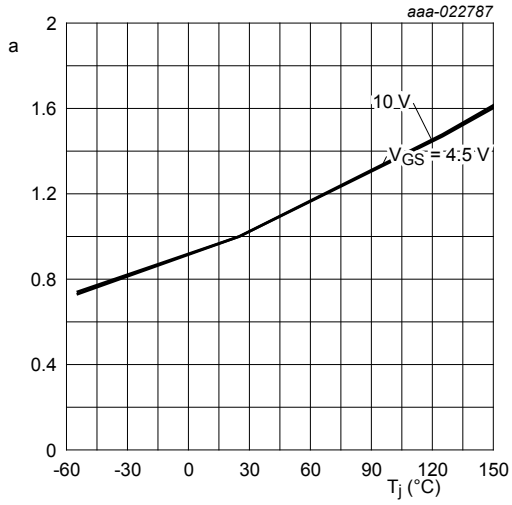
**Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values**



**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

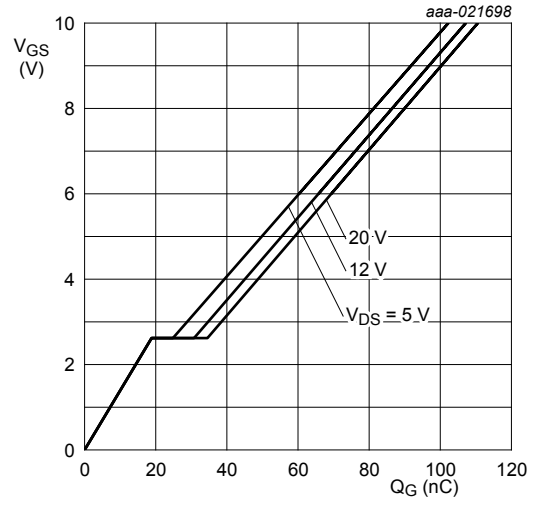


**Fig. 10. Drain-source on-state resistance as a function of drain current; typical values**



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature



$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

Fig. 12. Gate-source voltage as a function of gate charge; typical values

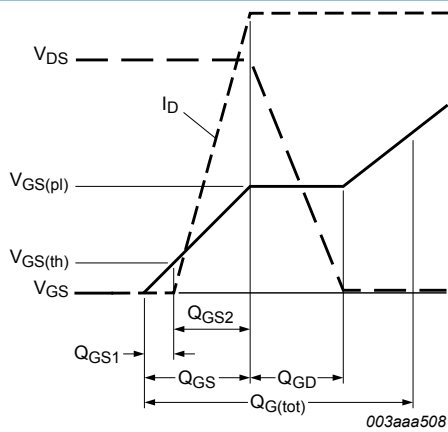
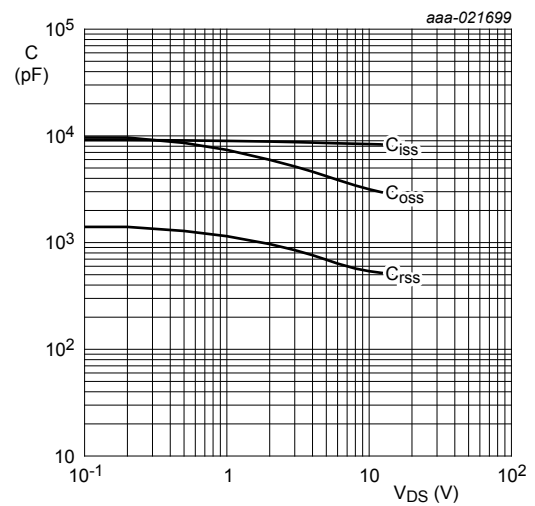


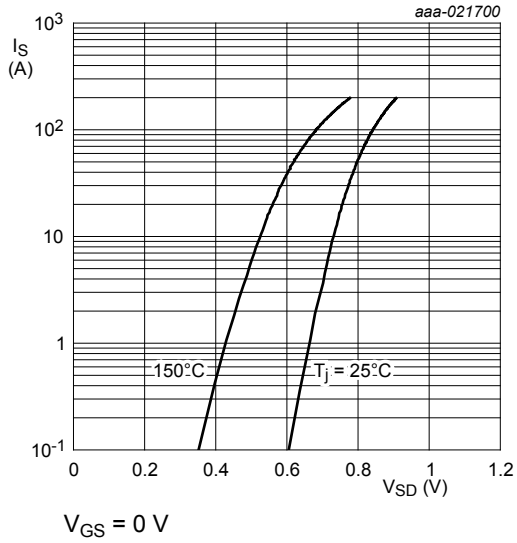
Fig. 13. Gate charge waveform definitions



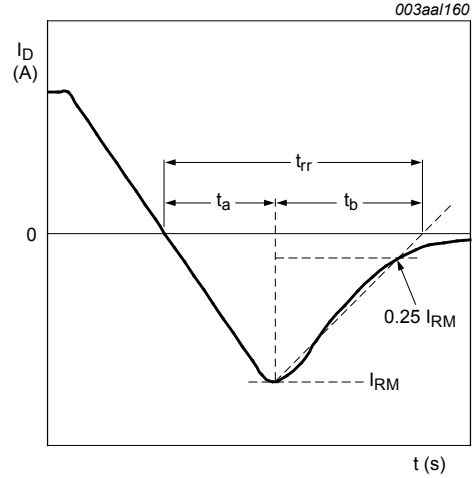
$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





**Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



**Fig. 16. Reverse recovery timing definition**

### 11. Package outline

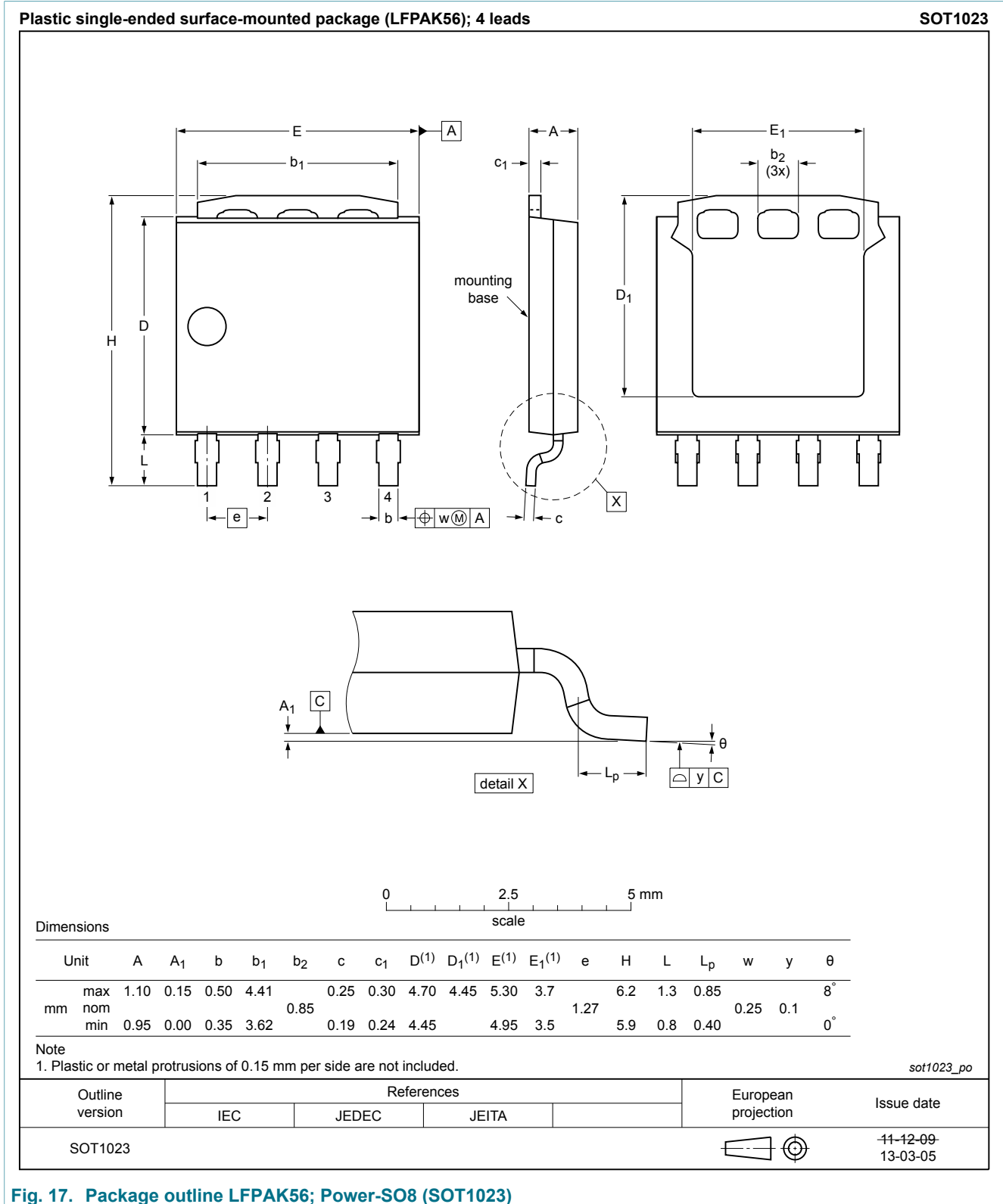
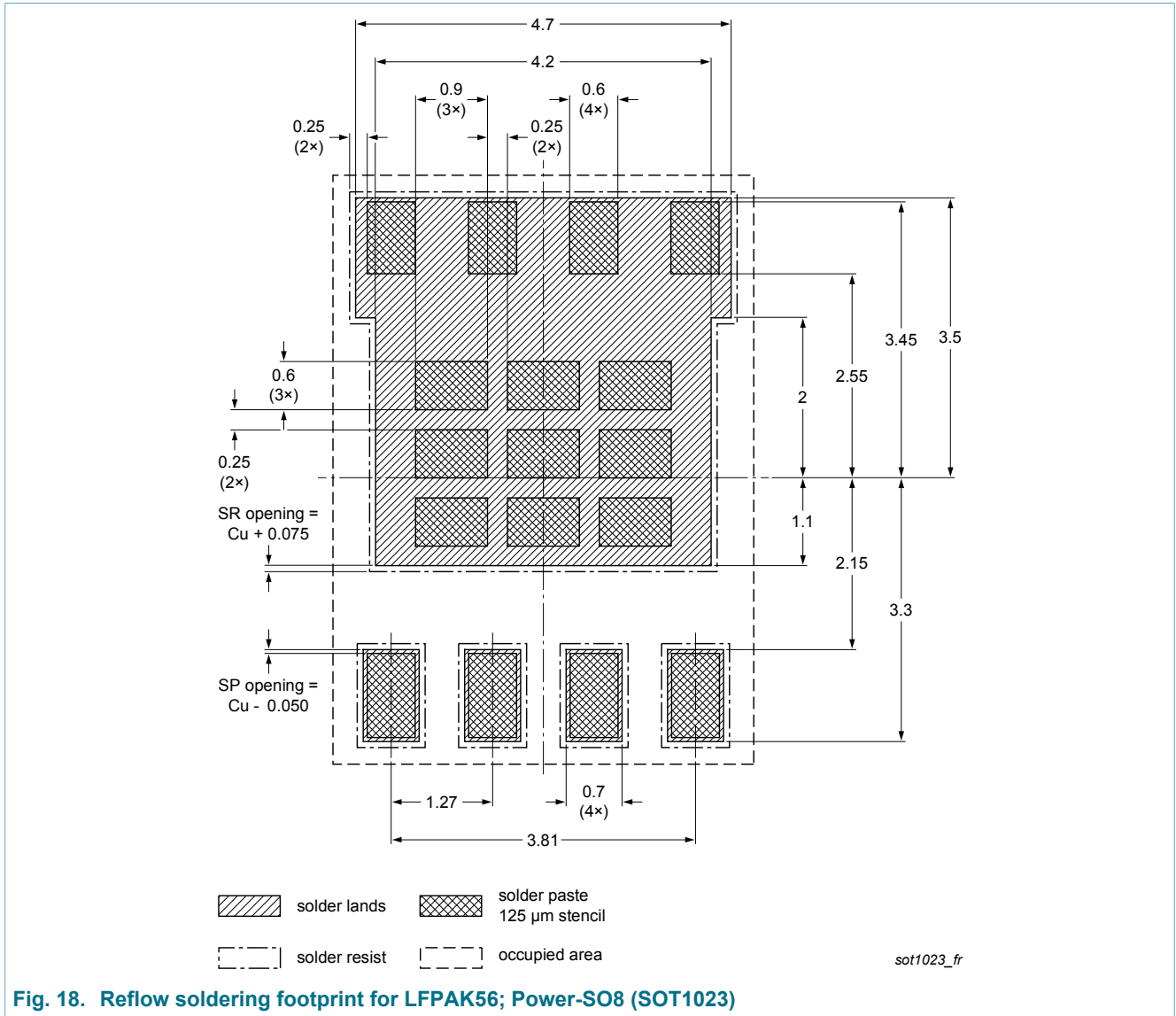


Fig. 17. Package outline LPAK56; Power-SO8 (SOT1023)

## 12. Soldering



## 13. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**N-channel 25 V, 0.72 mΩ, 300 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology**

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